

## TABLE OF CONTENTS

PREFACE	iii
ORGANIZATION OF SEVENTH SYMPOSIUM ON PLASMA PROCESSING	iv
MODELING, MECHANISMS, AND DIAGNOSTICS	
An Experimentalist's View of Plasma Modeling. Gottscho, R.A., Mitchell, A., Scheller, G.R., Schryer, N.L., Graves, D.B., and Boeuf, J.-P.	1
Parallel Plate Plasma Etching Reactor Model: Uniformity of Etching. Economou, D., Park, S.K., and Williams, G.	17
Modeling of Spatial Structure of Planar Magnetron Discharges. Lieberman, M.A., Wendt, A.E., and Gu, L.	35
Considerations for Building an Overall Dry Etching Process Simulator. Ignacio Ulacia F, J. and McVitte, J.P.	43
Simulation of Sheath Ion Transport Applied to the Time Evolution of Dry Etching Profiles. Ignacio Ulacia F, J. and McVitte, J.P.	50
Polymerization in CHF <sub>3</sub> Oxide Etch Discharges. Bariya, A.J., McVitte, J.P., de Larios, J.M., and Frank, C.W.	59
Plasma Etching of Silicon in SF <sub>6</sub> : Effect of Dis- charge Power and Electron Density on Etching Rate. Lii, Y.J., Jorne, J., Cadien, K.C., and Schoenholtz Jr., J.E.	67
Plasma Diagnostics by Mass Spectrometry. Vasile, M.J.	74
Light Emission from Chemically Assisted Ion Beam Etching (CAIBE) Processes. Glembocki, O.J., Palik, E.D., and McMarr, P.J.	84

#### REACTOR TECHNOLOGIES

High Density Plasma for Dry Processing. Mantei, T.D.	97
Microwave Plasma Processing: Some Uses in Device Fabrication. Wertheimer, M.R. and Klemberg-Sapieha, J.E.	110
Approaches to Low Energy Anisotropic Etching in Multipolar ECR Plasmas. Cooke, M.J., Graham, M., and Pelletier, J.	120
Remote Plasma Removal of Metallic Impurities from Silicon Surfaces. Frystak, D. and Ruzyllo, J.	125
Hollow Cathode Etching of Si and SiO <sub>2</sub> Using CF <sub>4</sub> and H <sub>2</sub> . Fortuno, G. and Oehrlein, G.S.	137

#### SURFACE DAMAGE AND MODIFICATION

Surface Modification of Electronic Materials by Plasma Etching. Oehrlein, G.S., Robey, S.W., Jaso, M.A., and Scilla, G.J.	151
Silicon Near-Surface Defects Induced by Hydrogen Plasma. Jeng, S.J., Oehrlein, G.S., and Scilla, G.J.	166
Behaviour of Carbon Impurities Introduced by Reactive Ion Etching. Kennedy, J., Ruzyllo, J., Houser, C., and Pantano, C.	170
The Effect of RIE Etching in CHF <sub>3</sub> /CO <sub>2</sub> Plasma and Successive Residual Damage Removal on the Contact Resistance of Al-nSi and Al+1%Si-nSi Contacts. Shenai, K., Al-Marayati, S., Saia, R., Lewis, N., Smith, G.A., and Baliga, B.J.	179

#### ETCHING AND DEPOSITION PROCESSES

Etching of Tungsten in Chlorine Containing Discharges. Fischl, D.S. and Hess, D.W.	194
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Promising Chlorofluoromethane Chemistries for Tungsten Etch. Daubenspeck, T.H., Sukanek, P., and White, E.J.	205
Tungsten Dry Etching in a Medium Pressure Single Wafer Etcher. Franssila, S.	228
Anisotropic Etching of Tungsten. Saito, T., Nakamura, M., and Yano, H.	240
BCl <sub>3</sub> /Cl <sub>2</sub> Reactive Ion Etching of Trenches. Robb, F.Y. and Sullivan, D.F.	250
The Influence of Carbonaceous Polymer on Leak Current in Trench Isolation. Samukawa, S., Eguchi, K., and Suganuma, T.	263
Development of a Helium/Chlorine Based Etch Process for Etching Polysilicon to Stop on Single Crystal Silicon. McOmber, J.I.	275
Plasma Etching of Polysilicon Doped by Ion Implantation. Karulkar, P.C. and Wirzbicki, M.A.	285
Plasma Floating Gate Etch Process for EEPROM's. Chang, P.C., Hu, J., and Chern, G.C.	294
Mask Dependent Etching with Fluorocarbon and Non-fluorocarbon Gases. Grynkewich, G.W., Fedynyshyn, T.H., and Chen, B.A.	303
Photoresist Reticulation Problems Associated with Plasma Etching. Hackenberg, J., Holbrook, B., and Ingwersen, T.	317
Role of Oxygen in the Prevention of Fence Formation During Aps Planarization. Hackenberg, J., Holbrook, B., Cronin, D., and Singlevich, S.	326
Via Planarization Application to a 0.9 um Two-Level Metal Technology. Hills, G.W. and Hey, H.P.W.	336

Equal Rate and Anisotropic Reactive Ion Etching of GaAs/AlGaAs Heterostructures in SiCl <sub>4</sub> Plasma. Salimian, S. and Cooper III, C.B.	344
Conduction in a-SiN:H and SiON:H Alloys. Osenbach, J.W., Knolle, W.R. and Elia, A.	352
Hybrid Gate Insulators for Amorphous Silicon TFT Application. Chen, H.-K., Wang, T.-S., Hao, C.-W., Wu, B.-S., and Wu, T.-K.	362
ARXPS Study of Sputter Deposition on Dielectrics: Damage, Epitaxy, and Growth. Halbritter, J., Hedbabny, H.J., and Rogalla, H.J.	368
Physical and Chemical Properties of Magnetron Sputtered Silicon Nitride Films. Carriere, T., Vickridge, I., Agius, B., Alnot, P., Seijka, J., and Joubard, R.	370
Deposition Profile Simulation Using Direct Simulation Monte Carlo Method. Ikegawa, M. and Kobayashi, J.	378
AUTHOR INDEX	391
SUBJECT INDEX	394